

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 1, line 3 with:

The present invention generally relates to ~~high-frequency~~ integrated circuit devices and, more particularly, to ~~a high-frequency~~ an integrated circuit device acting as a transmission power amplifier circuit for a code division multiple access (CDMA) modulation ~~type~~ portable terminal, in which a setting bias of an amplifier is ~~changed over~~ switched at the time of low power output and high power output and a bipolar transistor is employed for raising efficiency at the time of low power output.

Replace the paragraph beginning at page 1, line 10 with:

In the ~~a~~ transmission power amplifier circuit for the ~~a~~ CDMA modulation ~~type~~ portable terminal, since power control is performed during communication, high priority is given to not only ~~power~~ additional efficiency at the time of high power output but efficiency at the time of low power output. Thus, the amplifier is operated by changing over switching a setting bias of an amplifier at the time of low power output and high power output, ~~the amplifier is operated~~. Therefore, a conventional power amplifier circuit disclosed in, for example, Japanese Patent Laid-Open Publication No. 6-13816 (1994) includes a high-frequency transistor for amplifying a signal and a bias circuit for supplying a base bias to the high-frequency transistor such that a bias ~~changeover~~ switch for changing ~~over~~ a setting bias of the high-frequency transistor is provided in the bias circuit. Meanwhile, another known power amplifier circuit disclosed in, for example, Japanese Patent Laid-Open Publication No. 2001-274636 (2001) includes a bias circuit in which a bias generating circuit and a reference voltage generating circuit acting as a temperature compensation circuit for ~~performing~~ temperature compensation of the bias generating circuit are provided.